Part Number Customer						
Category	Parameter		Specification	Measurement Method		
OverallWafer	1.0	Diameter	100.00 +/- 0.20 mm			
	2.0	Primary Flat Orientation	{110} +/- 1 degree	Customer supplied material		
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Customer supplied material		
	4.0	Secondary Flat Orientation	none or SEMI Standard	Customer supplied material		
	5.0	Overall Thickness	371.00 +/- 6.00 μm	ADE, 100%		
	6.0	Total Thickness Variation (TTV)	<3.00µm	Guaranteed by Process		
	7.0	Bow	<60.00µm	ADE to ASTM F534, 100%		
	8.0	Warp	<60.00µm	ADE to ASTM F534, 100%		
	9.0	Edge Chips	0	Bright Light, 100%		
	10.0	Edge Exclusion	5mm			
HandleSilicon	11.0	Handle Growth Method	CZ	Customer supplied material		
	12.0	Handle Orientation	{100} +/- 0.5 degree	Customer supplied material		
	13.0	Handle Thickness	300.00 +/- 5.00 μm	ADE, 100%		
	14.0	Handle Doping Type	Р	Customer supplied material		
	15.0	Handle Dopant	Boron	Customer supplied material		
	16.0	Handle Resistivity	0.01-0.02 Ohm-cm	Customer supplied material		
	17.0	Backside Finish	Polished with oxide and lasermark	Guaranteed by process		
BuriedOxide	18.0	Oxide Type	Thermal			
	19.0	Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%		
	20.0	Oxide formed on	Device and/or Handle			
DeviceSilicon	21.0	Device Growth Method	CZ	Customer supplied material		
	22.0	Device Orientation	{100} +/- 0.5 degree	Customer supplied material		
	23.0	Nominal Thickness	70.00 +/- 1.00 μm	ADE single point, 100% (note3)		
	24.0	Distance to device silicon edge from wafer edge	< 2mm	Typical by Process		
	25.0	Device Doping Type	Р	Customer supplied material		
	26.0	Device Dopant	Boron	Customer supplied material		
	27.0	Device Resistivity	0.01-0.02 Ohm-cm	Customer supplied material		
	28.0	Surface Voids	None	Bright Light, 100% (note2)		
	29.0	Haze	None	Bright Light, 100% (note2)		
	30.0	Scratches	none on the front-side	Bright Light, 100% (note2)		

Icemos Technology Ltd

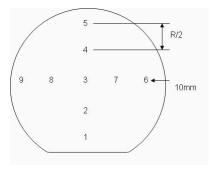
**Product Specification** 

1000.704904

Part Number			Customer		
	Category	Parameter	Specification	Measurement Method	
	Shipping Details	Wafer per box :	Max 25		
		Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging		
		Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
	Explanatory Notes	1. Microscope inspect	tion performed using microscope scan as below. 5x objective.		

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information